

SN74LVC1G66 Single Bilateral Analog Switch

1 Features

- Available in the Texas Instruments NanoFree™ Package
- 1.65V to 5.5V V_{CC} Operation
- Inputs Accept Voltages to 5.5V
- Max t_{pd} of 0.8ns at 3.3V
- High On-Off Output Voltage Ratio
- High Degree of Linearity
- High Speed, Typically 0.5ns ($V_{CC} = 3V$, $C_1 = 50pF$
- Low ON-State Resistance, Typically approximately $5.5\Omega (V_{CC} = 4.5V)$
- Latch-Up Performance Exceeds 100mA Per JESD 78, Class II
- **ESD Protection Exceeds JESD 22**
 - 2000V Human-Body Model (A114-A)
 - 200V Machine Model (A115-A)
 - 1000V Charged-Device Model (C101)

2 Applications

- Wireless Devices
- Audio and Video Signal Routing
- Portable Computing
- Wearable Devices
- Signal Gating, Chopping, Modulation or Demodulation (Modem)
- Signal Multiplexing for Analog-to-Digital and Digital-to-Analog Conversion Systems

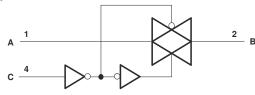
3 Description

The SN74LVC1G66 single, bilateral analog switch is designed for 1.65V to 5.5V V_{CC} operation, and supports both analog and digital signals. SN74LVC1G66 permits bidirectional transmission of signals with amplitudes of up to 5.5V (peak). By using the die as the package, NanoFree package technology represents a significant advancement in IC packaging concepts.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾
SN74LVC1G66DBV	DBV (SOT-23, 5)	2.90mm × 2.80mm
SN74LVC1G66DCK	DCK (SC70, 5)	2.00mm × 2.10mm
SN74LVC1G66DRL	DRL (SOT, 5)	1.60mm × 1.60mm
SN74LVC1G66DRY	DRY (SON, 6)	1.45mm × 1.00mm
SN74LVC1G66YZP	YZP (DSBGA, 5)	1.39mm × 0.89mm
SN74LVC1G66DSF	DSF (SON, 6)	1.00mm x 1.00mm

- For all available packages, see the orderable addendum at the end of the data sheet.
- The package size (length × width) is a nominal value and includes pins, where applicable.



Logic Diagram (Positive Logic)



Table of Contents

1 Features1	7.1 Overview	15
2 Applications 1	7.2 Functional Block Diagram	
3 Description1	7.3 Feature Description	
4 Pin Configuration and Functions3	7.4 Device Functional Modes	
Pin Functions4	8 Application and Implementation	16
Pin Functions4	8.1 Application Information	16
5 Specifications5	8.2 Typical Application	16
5.1 Absolute Maximum Ratings5	8.3 Power Supply Recommendations	17
5.2 ESD Ratings5	8.4 Layout	18
5.3 Recommended Operating Conditions6	9 Device and Documentation Support	19
5.4 Thermal Information6	9.1 Documentation Support	19
5.5 Electrical Characteristics7	9.2 Receiving Notification of Documentation Updates	19
5.6 Switching Characteristics: DBV, DCK7	9.3 Support Resources	19
5.7 Switching Characteristics: DRL, DRY, YZP, DSF8	9.4 Trademarks	19
5.8 Analog Switch Characteristics9	9.5 Electrostatic Discharge Caution	19
5.9 Operating Characteristics10	9.6 Glossary	19
5.10 Typical Characteristics10	10 Revision History	20
6 Parameter Measurement Information11	11 Mechanical, Packaging, and Orderable	
7 Detailed Description 15	Information	20



4 Pin Configuration and Functions

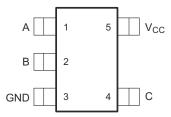


Figure 4-2. DCK Package 5-Pin SC70 (Top View)

Figure 4-1. DBV Package 5-Pin SOT-23 (Top View)

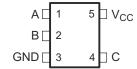


Figure 4-3. DRL Package 5-Pin SOT (Top View)

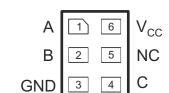


Figure 4-4. DSF Package 6-Pin X2SON (Top View)

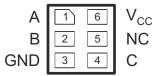


Figure 4-5. DRY Package 6-Pin USON (Top View)



Pin Functions

	PIN				
NAME	SOT NO.	USON, X2SON NO.	Type ⁽¹⁾	DESCRIPTION	
А	1	1	I/O	Bidirectional signal to be switched	
В	2	2	I/O	Bidirectional signal to be switched	
С	4	4	I	Controls the switch (L = OFF, H = ON)	
GND	3	3	_	Ground pin	
NC	_	5	_	Do not connect	
V _{CC}	5	6	_	Power pin	

(1) I = input; O = output; I/O = input or output

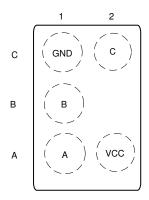


Figure 4-6. YZP Package 5-Pin DSBGA (BottomView)

Pin Functions

PIN		Type ⁽¹⁾	DESCRIPTION				
NAME	DSBGA NO.	Type	DESCRIPTION				
Α	A1	I/O	Bidirectional signal to be switched				
В	B1	I/O	Bidirectional signal to be switched				
С	C2	I	Controls the switch (L = OFF, H = ON)				
GND	C1	_	Ground pin				
V _{CC}	A2	_	Power pin				

(1) I = input; O = output; I/O = input or output

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	DCK, DBV Packages Supply voltage ⁽²⁾		-0.5	6	V
V _{CC}	DRL, DRY, YZP, DSF Packages Supply voltage ⁽²⁾			6.5	V
VI	DCK, DBV Packages Input voltage ^{(2) (3)}	-0.5	6	V	
VI	V _I DRL, DRY, YZP, DSF Packages Input voltage ^{(2) (3)}				V
V _{I/O}	Switch I/O voltage ^{(2) (3) (4)}				V
I _{IK}	Control input clamp current	V _I < 0		-50	mA
I _{IOK}	I/O port diode current	$V_{I/O}$ < 0 or $V_{I/O}$ > V_{CC}		±50	mA
I _T	ON-state switch current	$V_{I/O}$ < 0 to V_{CC}		±50	mA
	Continuous current through V _{CC} or GND			±100	mA
T _{stg}	stg Storage Temperature			150	°C
Tj	Junction Temperature			150	°C

Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

- (2) All voltages are with respect to ground, unless otherwise specified.
- (3) The input and output negative-voltage ratings can be exceeded if the input and output clamp-current ratings are observed.
- (4) This value is limited to 5.5V maximum.

5.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	+2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	+1000	V

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.



5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT	
V _{CC}	Supply voltage		1.65	5.5	V	
V _{I/O}	I/O port voltage.		0	V _{CC}	V	
		V _{CC} = 1.65V to 1.95V	V _{CC} × 0.65			
V	High-level input voltage, control input	V _{CC} = 2.3V to 2.7V	V _{CC} × 0.7		V	
V_{IH}		V _{CC} = 3V to 3.6V	V _{CC} × 0.7			
		V _{CC} = 4.5V to 5.5V	V _{CC} × 0.7			
		V _{CC} = 1.65V to 1.95V		V _{CC} × 0.35		
V	Low-level input voltage, control input	V _{CC} = 2.3V to 2.7V		V _{CC} × 0.3	V	
V_{IL}		V _{CC} = 3V to 3.6V		V _{CC} × 0.3	V	
		V _{CC} = 4.5V to 5.5V		V _{CC} × 0.3		
VI	Control input voltage		0	5.5	V	
		V _{CC} = 1.65V to 1.95V		20		
۸+/۸۰,	Control input transition rise and fall time	V _{CC} = 2.3V to 2.7V	20		ns/V	
Δι/Δν	Control input transition rise and fall time	V _{CC} = 3V to 3.6V		10	115/ V	
		V _{CC} = 4.5V to 5.5V		10		
T _A	DCK, DBV Packages Operating free-air temperature		-40	125	°C	
T _A	DRL, DRY, YZP, DSF Packages Operating free-air temperature		-40	85	°C	

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to provide proper device operation. See also, the *Implications of Slow or Floating CMOS Inputs* application note.

5.4 Thermal Information

		SN74LVC1G66							
	THERMAL METRIC(1)		DCK (SC70)	DRL (SOT)	DRY (USON)	DSF (X2SON)	YZP (DSBGA)	UNIT	
		5 PINS	5 PINS	5 PINS	6 PINS	6 PINS	5 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	262	313	142	355	348	132	°C/W	
R _θ JC(top)	Junction-to-case (top) thermal resistance	198	203	_	250	215	_	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	142	195	_	222	211	_	°C/W	
Ψ_{JT}	Junction-to-top characterization parameter	123	120	_	78	35	_	°C/W	
Ψ_{JB}	Junction-to-board characterization parameter	142	194	_	221	210	_	°C/W	

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application note.

5.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDIT	IONS	V _{cc}	MIN TYP(1)	MAX	UNIT
		V _I = V _{CC} or GND,	I _S = 4mA	1.65V	12	30	
r	ON-state switch resistance	$V_C = V_{IH}$	I _S = 8mA	2.3V	9	20	Ω
r _{on}	ON-State Switch resistance	(see Figure 6-1 and Figure 5-1)	I _S = 24mA	3V	7.5	15	12
		3-1)	I _S = 32mA	4.5V	5.5	10	
		V = V to CND	I _S = 4mA	1.65V	125	200	
r	DCK, DBV Packages Peak on	$V_I = V_{CC}$ to GND, $V_C = V_{IH}$	I _S = 8mA	2.3V	35	60	Ω
r _{on(p)}	resistance	(see Figure 6-1 and Figure 5-1)	I _S = 24mA	3V	11.5	25	32
			I _S = 32mA	4.5V	7.5	15	
			I _S = 4mA	1.65V	74.5	120	
	DRL, DRY, YZP, DSF Packages Peak	$V_I = V_{CC}$ to GND, $V_C = V_{IH}$	I _S = 8mA	2.3V	20	30	Ω
r _{on(p)}	on resistance	(see Figure 6-1 and Figure 5-1)	I _S = 24mA	3V	11.5	25	
		0-1)	I _S = 32mA	4.5V	7.5	15	
	OFF state switch is also as a surrent	V _I = V _{CC} and V _O = GND or				±1	
I _{S(off)}	OFF-state switch leakage current	$V_I = GND$ and $V_O = V_{CC}$, $V_C = V_{IL}$ (see Figure 6-2)	T _A = 25°C	5.5V		±0.1	μA
		$V_I = V_{CC}$ or $GND, V_C = V_{IH}$,				±1	μА
I _{S(on)}	ON-state switch leakage current	V _O = Open (see Figure 6-3)	T _A = 25°C	5.5V		±0.1	
I.	Control input current	$V_C = V_{CC}$ or GND		5.5V		±1	μA
l _l	Control input current	AC - ACC OL GIAD	T _A = 25°C	3.34		±0.1	μΑ
	Supply ourrent	V = V or CND		5.5V		10	
Icc	Supply current	$V_C = V_{CC}$ or GND	T _A = 25°C	3.50		1	μA
ΔI_{CC}	Supply current change	$V_C = V_{CC} - 0.6V$		5.5V		500	μA
C _{ic}	Control input capacitance			5V	2		pF
C _{io(off)}	Switch input and output capacitance			5V	6		pF
C _{io(on)}	DCK, DBV Packages Switch input and output capacitance			5V	15		pF
C _{io(on)}	DRL, DRY, YZP, DSF Packages Switch input and output capacitance			5V	13		pF

(1) $T_A = 25^{\circ}C$

5.6 Switching Characteristics: DBV, DCK

over operating free-air temperature range of T_A = -40 to +125°C

PARAMETER		FROM (INPUT)	TO (OUTPUT)	V _{CC} = ± 0.1		V _{CC} = ± 0.		V _{CC} = ± 0.		V _{CC} = ± 0.9		UNIT
	(INFOT)	(0011-01)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
	t _{pd} ⁽¹⁾	A or B	B or A		2.2		1.2		0.8		0.6	ns
	t _{en} ⁽²⁾	С	A or B	2.5	12	1.9	6.5	1.8	5	1.5	4.2	ns
	t _{dis} (3)	С	A or B	2.2	11.5	1.4	6.9	2	6.5	1.4	6	ns

⁽¹⁾ t_{PLH} and t_{PHL} are the same as t_{pd} . The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

⁽²⁾ t_{PZL} and t_{PZH} are the same as t_{en} .

⁽³⁾ t_{PLZ} and t_{PHZ} are the same as t_{dis} .



5.7 Switching Characteristics: DRL, DRY, YZP, DSF

over operating free-air temperature range of T_A = -40 to +85°C

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = ± 0.1		V _{CC} = ± 0.		V _{CC} = ± 0.		V _{CC} = ± 0.9		UNIT
	(INFOT)	(0011-01)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd} (1)	A or B	B or A		2		1.2		0.8		0.6	ns
t _{en} (2)	С	A or B	2.5	12	1.9	6.5	1.8	5	1.5	4.2	ns
t _{dis} (3)	С	A or B	2.2	10	1.4	6.9	2	6.5	1.4	5	ns



5.8 Analog Switch Characteristics

 $T_A = 25^{\circ}C$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V _{cc}	TYP	UNIT
				1.65V	35	
			$C_L = 50 \text{pF}, R_L = 600 \Omega,$ $f_{\text{in}} = \text{sine wave}$	2.3V	120	
		B or A	(see Figure 6-5)	3V	175	
Frequency response ⁽¹⁾ (switch	A or B			4.5V	195	MHz
ON)	AOIB	BOIA		1.65V	>300	IVII IZ
			$C_L = 5pF, R_L = 50\Omega,$ $f_{in} = sine wave$	2.3V	>300	
			(see Figure 6-5)	3V	>300	
				4.5V	>300	
				1.65V		
Crosstalk	С	A or B	$C_L = 50$ pF, $R_L = 600\Omega$, $f_{in} = 1$ MHz (square wave)	2.3V	50	mV
(control input to signal output)		AOIB	(see Figure 6-6)	3V	70	111 V
				4.5V	100	
				1.65V	-58	
		B or A	C_L = 50pF, R_L = 600 Ω , f_{in} = 1MHz (sine wave) (see Figure 6-7)	2.3V	-58	dB
				3V	-58	
Feedthrough attenuation ⁽²⁾	A or B			4.5V	-58	
switch OFF)	AUID			1.65V	-42	
			$C_L = 5pF, R_L = 50\Omega,$ $f_{in} = 1MHz (sine wave)$	2.3V	-42	
			(see Figure 6-7)	3V	-42	
				4.5V	-42	
				1.65V	0.5	
			C_L = 50pF, R_L = 10k Ω , f_{in} = 1kHz (sine wave) (see Figure 6-8)	2.3V	0.025	- 1
				3V	0.015	
DCK, DBV Packages Sine-	A or B	B or A		4.5V	0.01	%
wave distortion	AOID	BOIA		1.65V	0.15	70
			$C_L = 50 \text{pF}, R_L = 10 \text{k}\Omega,$ $f_{\text{in}} = 10 \text{kHz} \text{ (sine wave)}$	2.3V	0.025	
			(see Figure 6-8)	3V	0.015	
				4.5V	0.01	
				1.65V	0.1	
			$C_L = 50 \text{pF}, R_L = 10 \text{k}\Omega,$	2.3V	0.025	
			t _{in} = 1kHz (sine wave) (see Figure 6-8)	3V	0.015	%
DRL, DRY, YZP, DSF	A or B	B or A		4.5V	0.01	
Packages Sine-wave distortion	A OF B	D OF A		1.65V	0.15	
			C_L = 50pF, R_L = 10k Ω , f_{in} = 10kHz (sine wave) (see Figure 6-8)	2.3V	0.025	
				3V	0.015	
				4.5V	0.01	

⁽¹⁾ Adjust f_{in} voltage to obtain 0dBm at output. Increase f_{in} frequency untildB meter reads –3dB. (2) Adjust f_{in} voltage to obtain 0dBm at input.



5.9 Operating Characteristics

 $T_A = 25^{\circ}C$

	PARAMETER	TEST	V _{CC} = 1.8V	V _{CC} = 2.5V	V _{CC} = 3.3V	V _{CC} = 5V	UNIT
	PANAMETER	CONDITIONS	TYP	TYP	TYP	TYP	ONT
C_{pd}	Power dissipation capacitance	f = 10MHz	8	9	9	11	pF

5.10 Typical Characteristics

 $T_A = 25^{\circ}C$

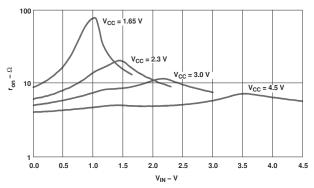


Figure 5-1. Typical r_{on} as a Function of Input Voltage (V_I) for V_{I} = 0 to V_{CC}



6 Parameter Measurement Information

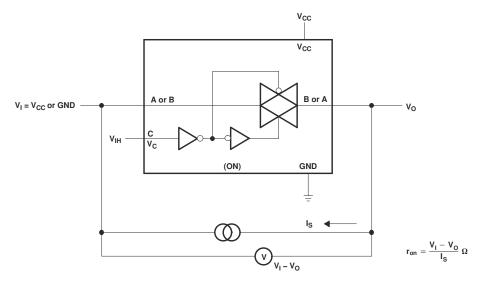


Figure 6-1. ON-State Resistance Test Circuit

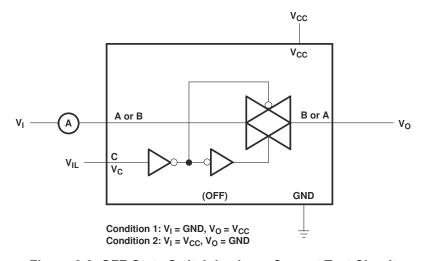


Figure 6-2. OFF-State Switch Leakage-Current Test Circuit

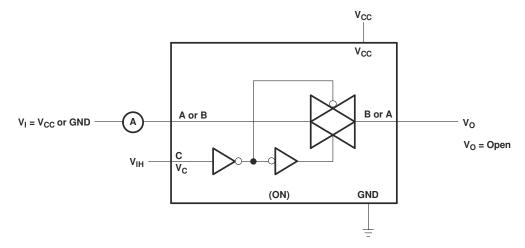
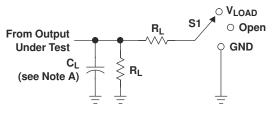


Figure 6-3. ON-State Switch Leakage-Current Test Circuit

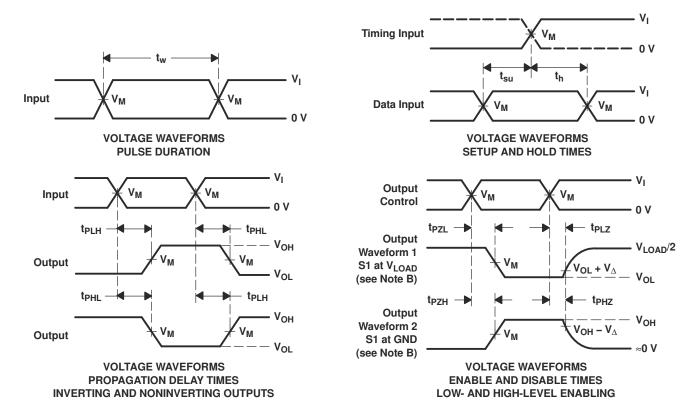




TEST	S1
t _{PLH} /t _{PHL}	Open
t_{PLZ}/t_{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

V	INPUTS		V	V	0	В	V
V _{CC}	VI	t _r /t _f	V _M	V _{LOAD}	CL	R _L	V_{Δ}
1.8 V ± 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2×V _{CC}	30 pF	1 k Ω	0.15 V
2.5 V \pm 0.2 V	V _{CC}	≤2 ns	V _{CC} /2	2 × V _{CC}	30 pF	500 Ω	0.15 V
3.3 V \pm 0.3 V	V _{CC}	≤2.5 ns	V _{CC} /2	2 × V _{CC}	50 pF	500 Ω	0.3 V
5 V \pm 0.5 V	V _{CC}	≤2.5 ns	V _{CC} /2	2 × V _{CC}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 6-4. Load Circuit and Voltage Waveforms

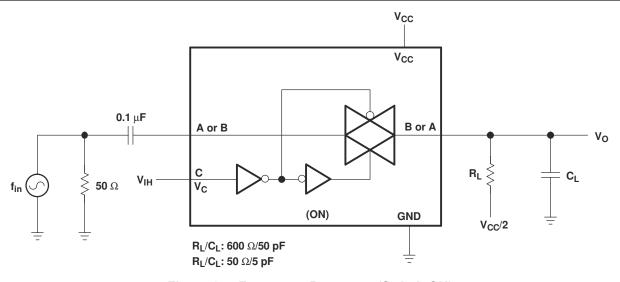


Figure 6-5. Frequency Response (Switch ON)

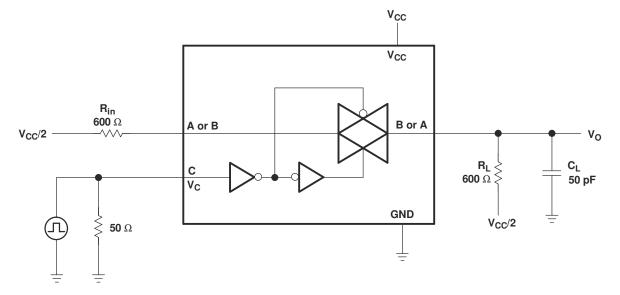


Figure 6-6. Crosstalk (Control Input – Switch Output)



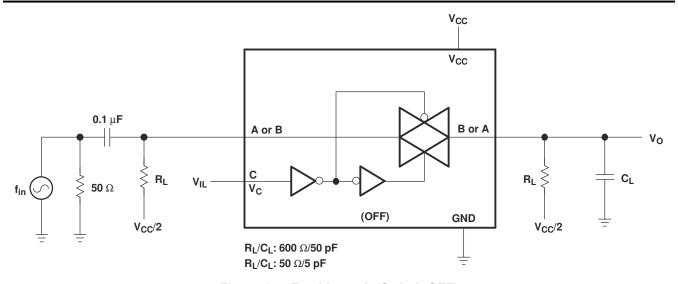


Figure 6-7. Feedthrough (Switch OFF)

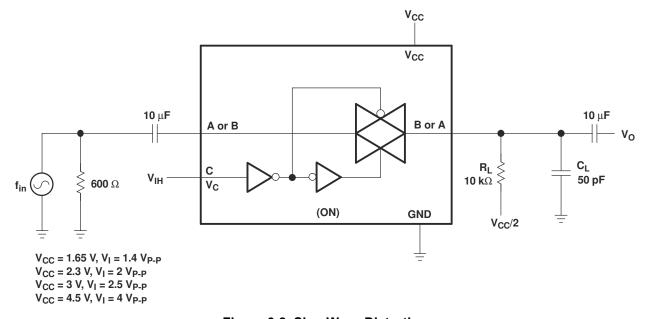


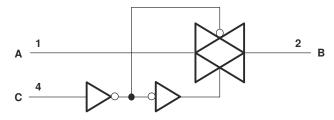
Figure 6-8. Sine-Wave Distortion

7 Detailed Description

7.1 Overview

The SN74LVC1G66 single, bilateral analog switch is designed for 1.65V to 5.5V V_{CC} operation, and supports both analog and digital signals. SN74LVC1G66 permits bidirectional transmission of signals with amplitudes of up to 5.5V (peak). By using the die as the package, NanoFree package technology represents a significant advancement in IC packaging concepts.

7.2 Functional Block Diagram



Logic Diagram (Positive Logic)

7.3 Feature Description

The TI NanoFree package is one of TI's smallest packages, which enables customers to save board space. The solder bumps enable easy testing. The SN74LVC1G66 has a wide V_{CC} range, enabling rail-to-rail operation of signals anywhere from a 1.8V to a 5V system. In addition, the control input (C Pin) tolerates up to 5.5V, enabling higher-voltage logic to interface to the switch control system.

7.4 Device Functional Modes

Table 7-1. Function Table

CONTROL INPUT (C)	SWITCH
L	OFF
Н	ON

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The SN74LVC1G66 can be used in any application where an SPST switch is used and a solid-state, voltage-controlled version is preferred.

8.2 Typical Application

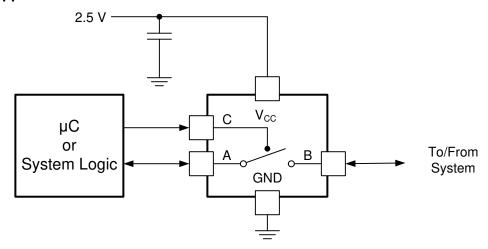


Figure 8-1. Typical Application Schematic

8.2.1 Design Requirements

The SN74LVC1G66 enables on and off control of analog and digital signals with a digital control signal. All input signals must remain between 0V and V_{CC} for optimal operation.

8.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions:
 - For rise time and fall time specifications, see Δt/Δv in Section 5.3.
 - For specified high and low levels, see V_{IH} and V_{IL} in Section 5.3.
 - Inputs and outputs are overvoltage tolerant allowing them to go as high as 5.5V at any valid V_{CC} .
- 2. Recommended Output Conditions:
 - Load currents must not exceed ±50mA.
- 3. Frequency Selection Criterion:
 - Maximum frequency tested is 150MHz.
 - Added trace resistance/capacitance can reduce maximum frequency capability; use layout practices as directed in Section 8.4.

8.2.3 Application Curve

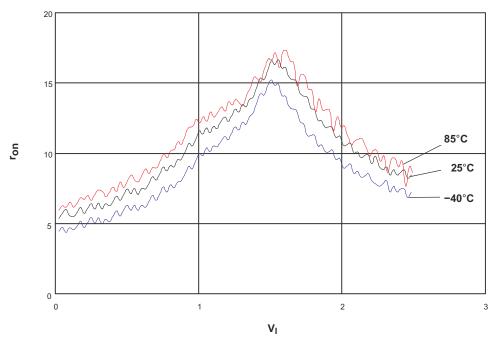


Figure 8-2. $r_{on} vsV_I, V_{CC} = 2.5V (SN74LVC1G66)$

8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in Section 5.3.

Each V_{CC} terminal must have a bypass capacitor to prevent power disturbance. For devices with a single supply, a $0.1\mu F$ bypass capacitor is recommended. If there are multiple pins labeled V_{CC} , then a $0.01\mu F$ or $0.022\mu F$ capacitor is recommended for each V_{CC} because the V_{CC} pins are connected internally. For devices with dual supply pins operating at different voltages (for example V_{CC} and V_{DD}), a $0.1\mu F$ bypass capacitor is recommended for each supply pin. Having parallel multiple bypass capacitors is acceptable to reject different frequencies of noise. $0.1\mu F$ and $1\mu F$ capacitors are commonly used in parallel. The bypass capacitor must be installed as close to the power terminal as possible for best results.



8.4 Layout

8.4.1 Layout Guidelines

Reflections and matching are closely related to loop antenna theory, but different enough to warrant a separate discussion. When a PCB trace turns a corner at a 90 degree angle, a reflection can occur. This occurs primarily due to the change of width of the trace. At the apex of the turn, the trace width is increased to 1.414 times the width. This upsets the transmission line characteristics — especially the distributed capacitance and self–inductance of the trace — resulting in the reflection.

Note

Not all PCB traces can be straight, and so can require turning corners. Figure 8-3 shows progressively better techniques of rounding corners. Only the last example maintains constant trace width and minimizes reflections.

8.4.2 Layout Example

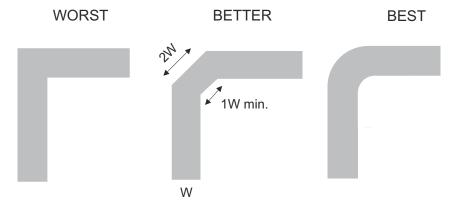


Figure 8-3. Trace Example



9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

· Texas Instruments, Implications of Slow or Floating CMOS Inputs

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

9.4 Trademarks

NanoFree[™] and TI E2E[™] are trademarks of Texas Instruments. All trademarks are the property of their respective owners.

9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.



10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision Q (March 2017) to Revision R (September 2025)	Page
Updated the numbering format for tables, figures, and cross-references throughout the number of tables.	ut the document1
Updated Thermal Information	
Updated resistance range in Section 5.5	
Updated switching timing in Section 5.6	
Updated Sine-wave distortion in Section 5.8	
 Added Receiving Notifications of Documentation Updates, Support Resources, E. 	
Caution, and Glossary the sections	
Changes from Revision P (March 2016) to Revision Q (March 2017)	Page
Changed the YZP package pin out graphic	4
Changes from Revision O (March 2015) to Revision P (March 2016)	Page
 Added Junction temperature specification to Absolute Maximum Ratings table 	
 Added Junction temperature specification to Absolute Maximum Ratings table Added "Control" to "Input transition rise and fall time" in Recommended Operating 	
 Added Junction temperature specification to Absolute Maximum Ratings table Added "Control" to "Input transition rise and fall time" in Recommended Operating Changes from Revision N (December 2012) to Revision O (March 2015) 	g Conditions table
 Added Junction temperature specification to Absolute Maximum Ratings table Added "Control" to "Input transition rise and fall time" in Recommended Operating 	Page cription section, Device amendations section, Layout
 Added Junction temperature specification to Absolute Maximum Ratings table Added "Control" to "Input transition rise and fall time" in Recommended Operating Changes from Revision N (December 2012) to Revision O (March 2015) Added Pin Configuration and Functions section, ESD Ratings table, Feature Descriptional Modes, Application and Implementation section, Power Supply Recoms section, Device and Documentation Support section, and Mechanical, Packaging section 	Page cription section, Device amendations section, Layour and Orderable Information
 Added Junction temperature specification to Absolute Maximum Ratings table Added "Control" to "Input transition rise and fall time" in Recommended Operating Changes from Revision N (December 2012) to Revision O (March 2015) Added Pin Configuration and Functions section, ESD Ratings table, Feature Desc Functional Modes, Application and Implementation section, Power Supply Recoms section, Device and Documentation Support section, and Mechanical, Packaging section Removed Ordering Information table 	Page cription section, Device amendations section, Layout and Orderable Information
 Added Junction temperature specification to Absolute Maximum Ratings table Added "Control" to "Input transition rise and fall time" in Recommended Operating Changes from Revision N (December 2012) to Revision O (March 2015) Added Pin Configuration and Functions section, ESD Ratings table, Feature Descriptional Modes, Application and Implementation section, Power Supply Recommendation, Device and Documentation Support section, and Mechanical, Packaging section 	Page cription section, Device amendations section, Layour and Orderable Information
 Added Junction temperature specification to Absolute Maximum Ratings table Added "Control" to "Input transition rise and fall time" in Recommended Operating Changes from Revision N (December 2012) to Revision O (March 2015) Added Pin Configuration and Functions section, ESD Ratings table, Feature Descruptional Modes, Application and Implementation section, Power Supply Recomsection, Device and Documentation Support section, and Mechanical, Packaging section Removed Ordering Information table Added Device Information table 	Page cription section, Device amendations section, Layour and Orderable Information
 Added Junction temperature specification to Absolute Maximum Ratings table Added "Control" to "Input transition rise and fall time" in Recommended Operating Changes from Revision N (December 2012) to Revision O (March 2015) Added Pin Configuration and Functions section, ESD Ratings table, Feature Desc Functional Modes, Application and Implementation section, Power Supply Recoms section, Device and Documentation Support section, and Mechanical, Packaging section Removed Ordering Information table	Page cription section, Device and Orderable Information Page
 Added Junction temperature specification to Absolute Maximum Ratings table Added "Control" to "Input transition rise and fall time" in Recommended Operating Changes from Revision N (December 2012) to Revision O (March 2015) Added Pin Configuration and Functions section, ESD Ratings table, Feature Descriptional Modes, Application and Implementation section, Power Supply Recommendation, Device and Documentation Support section, and Mechanical, Packaging section	Page cription section, Device and Orderable Information Page
 Added Junction temperature specification to Absolute Maximum Ratings table Added "Control" to "Input transition rise and fall time" in Recommended Operating Changes from Revision N (December 2012) to Revision O (March 2015) Added Pin Configuration and Functions section, ESD Ratings table, Feature Dest Functional Modes, Application and Implementation section, Power Supply Recomsection, Device and Documentation Support section, and Mechanical, Packaging section	Page cription section, Device amendations section, Layour and Orderable Information Page

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com

7-Oct-2025

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
SN74LVC1G66DBVR	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	(C665, C66J, C66R, C66T)
SN74LVC1G66DBVR.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(C665, C66J, C66R, C66T)
SN74LVC1G66DBVR.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(C665, C66J, C66R, C66T)
SN74LVC1G66DBVT	Obsolete	Production	SOT-23 (DBV) 5	-	-	Call TI	Call TI	-40 to 85	(C665, C66J, C66R)
SN74LVC1G66DCKR	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	(C65, C6F, C6J, C6 K, C6O, C6R, C 6T)
SN74LVC1G66DCKR.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(C65, C6F, C6J, C6 K, C6O, C6R, C 6T)
SN74LVC1G66DCKR.B	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(C65, C6F, C6J, C6 K, C6O, C6R, C 6T)
SN74LVC1G66DRLR	Active	Production	SOT-5X3 (DRL) 5	4000 LARGE T&R	Yes	NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	(C67, C6R)
SN74LVC1G66DRLR.A	Active	Production	SOT-5X3 (DRL) 5	4000 LARGE T&R	Yes	NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	(C67, C6R)
SN74LVC1G66DRLR.B	Active	Production	SOT-5X3 (DRL) 5	4000 LARGE T&R	Yes	NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	(C67, C6R)
SN74LVC1G66DRYR	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C6
SN74LVC1G66DRYR.A	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C6
SN74LVC1G66DRYR.B	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C6
SN74LVC1G66DSF2	Obsolete	Production	SON (DSF) 6	-	-	Call TI	Call TI	-40 to 85	C6
SN74LVC1G66DSFR	Active	Production	SON (DSF) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C6
SN74LVC1G66DSFR.A	Active	Production	SON (DSF) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C6
SN74LVC1G66DSFR.B	Active	Production	SON (DSF) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C6
SN74LVC1G66YZPR	Active	Production	DSBGA (YZP) 5	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	C6N
SN74LVC1G66YZPR.B	Active	Production	DSBGA (YZP) 5	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	C6N

⁽¹⁾ Status: For more details on status, see our product life cycle.

PACKAGE OPTION ADDENDUM

www.ti.com 7-Oct-2025

(2) Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

- (3) RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.
- (4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.
- (5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.
- (6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC1G66:

Automotive: SN74LVC1G66-Q1

NOTE: Qualified Version Definitions:

Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects



www.ti.com 14-Dec-2024

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G66DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74LVC1G66DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G66DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3
SN74LVC1G66DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC1G66DSFR	SON	DSF	6	5000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
SN74LVC1G66YZPR	DSBGA	YZP	5	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1



www.ti.com 14-Dec-2024



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G66DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G66DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G66DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0
SN74LVC1G66DRYR	SON	DRY	6	5000	184.0	184.0	19.0
SN74LVC1G66DSFR	SON	DSF	6	5000	210.0	185.0	35.0
SN74LVC1G66YZPR	DSBGA	YZP	5	3000	220.0	220.0	35.0



DIE SIZE BALL GRID ARRAY



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.5. Lead width does not comply with JEDEC.
- 6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side





NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 10. Board assembly site may have different recommendations for stencil design.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.









NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.





NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).





NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC registration MO-287, variation X2AAF.





NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).





4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





PLASTIC SMALL OUTLINE



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-293 Variation UAAD-1



PLASTIC SMALL OUTLINE



NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PLASTIC SMALL OUTLINE



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2025. Texas Instruments Incorporated